MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Brodnet data speet

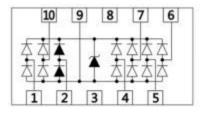
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PACKAGE OUTLINE



DFN4120-10

CIRCUIT DIAGRAM



FEATURES

♦Transient protection for high-speed data lines IEC 61000-4-2(ESD) ±20KV(Contact) ±25KV(Air)

IEC 61000-4-4(EFT) 40A(5/50ns) Cable Discharge Event (CDE)

- ♦Package optimized for high-speed lines
- ♦Small package (4.1mm*2.0mm*0.5mm)
- ♦Protects six data lines and one Vcc line
- ♦Low capacitance: 0.2pF (I/O to I/O)
- ♦Low leakage current
- ♦Low clamping voltage
- ♦Each I/O pin can withstand over 1000 ESD strikes for ±8KV contact discharge

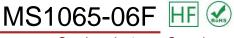
MACHANICAL DATA

- ♦DFN4120-10 package
- ♦Flammability Rating: UL 94V-0
- ♦Packaging: Tape and Reel
- ♦High temperature soldering guaranteed: 260C/10s
- ♦Reel size: 7 inch

APPLICATIONS

- ♦USB3.0
- ♦HDMI1.4
- ♦High Speed I/O Ports in any electronic product





Semiconductor Compiance

ABSOLUTE MAXIMUM RATING

Symbol	Parameter	Value	Units
P _{PP}	Peak Pulse Power (8/20µs)	60	W
Vesd	ESD per IEC 61000-4-2 (Contact) ESD per IEC 61000-4-2 (Air)	±20 ±25	kV
Торт	Operating Temperature	-55/+125	OC
Тѕтс	Storage Temperature	-55/+150	OC

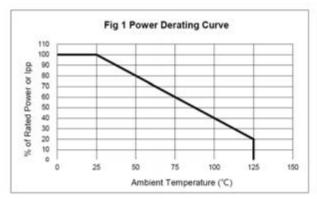
Symbol	Parameter	Test Condition	Min	Тур	Max	Units
VRWM	Reverse Working Voltage	Any I/O or Vcc pin to GND			5.0	V
VBR	Reverse Breakdown Voltage	Iτ = 1mA Any I/O or Vcc pin to GND	6.0		9.0	V
lr	Reverse Leakage Current	V _{RWM} = 5V Any I/O or Vcc pin to GND			1.0	РД
Vc	Clamping Voltage	I _{PP} = 1A, t _P = 8/20μs Any I/O pin to GND			10	V
		IPP = $4A$, $t_p = 8/20 \mu s$ Any I/O pin to GND			15	V
		IPP = 8A, t_P = 8/20 μ s Vcc pin to GND			15	V
Vctlp	TLP Clamping Voltage	IPP = 8A IEC61000-4-2 Level 2 equivalent (±4kV Contact, ±8kV Air) Between I/O and GND		16		V
		IPP = 16A IEC61000-4-2 Level 4 equivalent (±8kV Contact, ±16kV Air) Between I/O and GND		23		V
Cesd	Parasitic Capacitance	V _R = 0V, f = 1MHz Between I/O and I/O		0.2	0.3	pF
		V _R = 0V, f = 1MHz Between I/O and GND		0.4	0.5	pF
		V _R = 0V, f = 1MHz Between Vcc and GND		0.80		pF

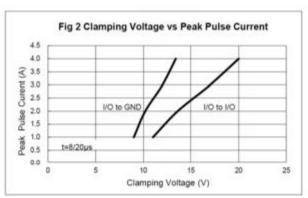
Note: I/O are pin 1,4,5,6,7,10; Vcc is pin 2; GND are pin9 and heatsink.

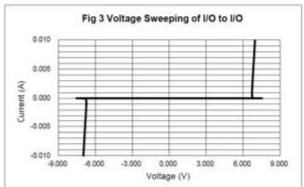


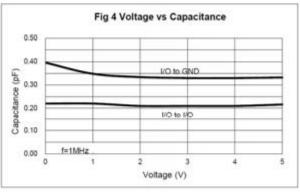


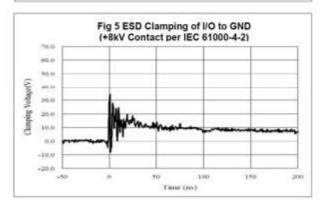
ELECTRICAL CHARACTERISTICS CURVE

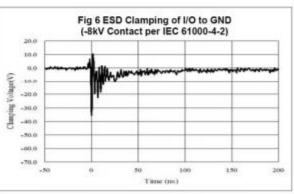


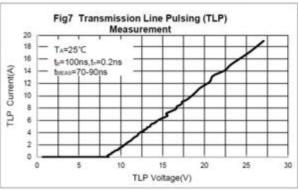




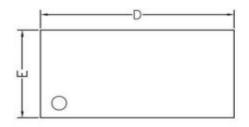


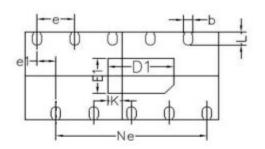


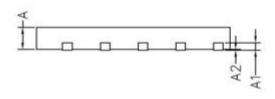




DFN4120-10L PACKAGE OUTLINE DIMENSIONS







0	Dimensions (mm)			
Symbol	Min.	Nom.	Max.	
А	0.45	0.50	0.55	
A1	0.15 REF			
A2	0.00	0.02	0.05	
D	4.05	4.10	4.15	
E	1.95	2.00	2.05	
D1	1.35	1.40	1.45	
E1	0.75	0.80	0.85	
L	0.25	0.30	0.35	
b	0.15	0.20	0.25	
е	0.80 BSC			
Ne	3.20 BSC			
e1	0.40 BSC			
К	0.25	0.30	0.35	

REEL SPECIFICATION

P/N	PKG	QTY
MS1065-06F	DFN4120-10	3000



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